

/ Descriptions

WR0<5 M M E SQS æ M ç s ll 1 Silicon PNP transistor in a TO-92 Plastic Package.

/ Features

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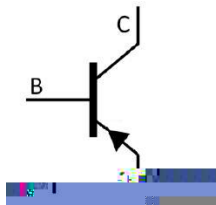
Low Leakage current, Low collector saturation voltage.

/ Applications

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General amplifier.

/ Equivalent Circuit



/ Pinning



PIN1 ç Collector PIN 2 ç Base PIN 3 ç Emitter

/ hFE Classifications & Marking

ø M ç ç ç See Marking Instructions.

2N2907

Rev. G .Aug.-2018



蓝箭电子
BLUE ROCKET ELECTRONICS

DATA SHEET

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-40	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-600	mA
Collector Power Dissipation	$P_{CCollector}$	78.22.1	ent

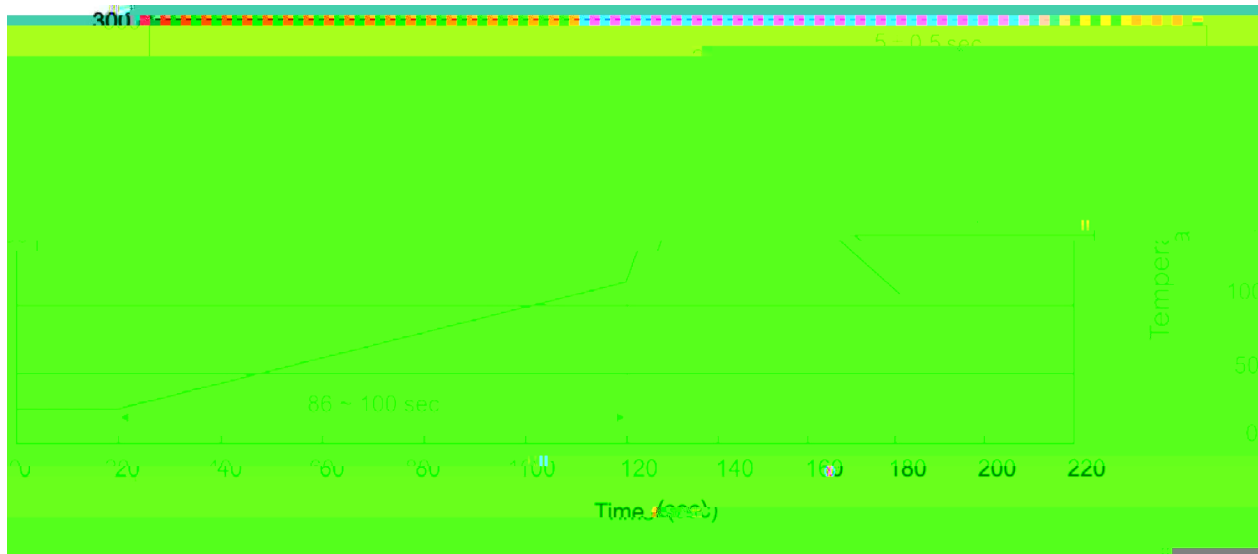
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() / Temperature Profile for Dip Soldering(Pb-Free)


说明

1. 预加热: 25~150℃, 时间: 60~90sec;
2. 峰值温度: 255±5℃, 时间: 5~0.5sec;
3. 冷却速度: 2~10℃/sec.

Note:

1. Preheating: 25~150℃, Time: 60~90sec.
2. Peak Temp.: 255±5℃, Duration: 5~0.5sec.
3. Cooling Speed: 2~10℃/sec.

/ Resistance to Soldering Heat Test Conditions

温度: 270±5℃ 时间: 10±1 sec. Temp: 270±5 Time: 10±1 sec

/ Packaging SPEC.

散装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-92	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195
	1,000	10	10,000	10	100,000	135×190	237×172×102	560×245×375

纸带 / AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	Units/tape 只/纸带	Tape/Inner Box 纸带/盒	Rows/Inner Box 纸带层/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Inner Box 盒	Outer Box 箱
TO-92	3,000	1	120	10	30,000	328×230×42	小箱 480×346×235, 大箱 547×407×268

/ Notices